

K L Wang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

273
papers

7,212
citations

47
h-index

70
g-index

284
ext. papers

7,686
ext. citations

3
avg, IF

5.41
L-index

#	Paper	IF	Citations
273	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 6752-6760	9.5	10
272	Field-Free Switching of Perpendicular Magnetization through Voltage-Gated Spin-Orbit Torque 2019 ,		15
271	Perpendicular magnetic tunnel junction with W seed and capping layers. <i>Journal of Applied Physics</i> , 2017 , 121, 153902	2.5	17
270	Strain induced exchange-spring magnetic behavior in amorphous (TbDy)Fe ₂ thin films. <i>Journal of Applied Physics</i> , 2017 , 121, 043911	2.5	5
269	A Spintronic Voltage-Controlled Stochastic Oscillator for Event-Driven Random Sampling. <i>IEEE Electron Device Letters</i> , 2017 , 38, 281-284	4.4	9
268	Analog to Stochastic Bit Stream Converter Utilizing Voltage-Assisted Spin Hall Effect. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1343-1346	4.4	11
267	Oscillatory magnetic anisotropy and spin-reorientation induced by heavy-metal cap in Cu/FeCo/M (M=Hf or Ta): A first-principles study. <i>Physical Review B</i> , 2016 , 94,	3.3	3
266	Ultra-low switching energy and scaling in electric-field-controlled nanoscale magnetic tunnel junctions with high resistance-area product. <i>Applied Physics Letters</i> , 2016 , 108, 012403	3.4	131
265	Electric-field-driven magnetization switching and nonlinear magnetoelasticity in Au/FeCo/MgO heterostructures. <i>Scientific Reports</i> , 2016 , 6, 29815	4.9	38
264	In-plane magnetic field effect on switching voltage and thermal stability in electric-field-controlled perpendicular magnetic tunnel junctions. <i>AIP Advances</i> , 2016 , 6, 075014	1.5	15
263	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. <i>Physical Review B</i> , 2016 , 94,	3.3	16
262	Giant voltage modulation of magnetic anisotropy in strained heavy metal/magnet/insulator heterostructures. <i>Physical Review B</i> , 2015 , 92,	3.3	69
261	Characterization of Trapped Charge in Ge/LixGe Core/Shell Structure during Lithiation using Off-axis Electron Holography. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1397-1398	0.5	
260	Electric field control and effect of Pd capping on magnetocrystalline anisotropy in FePd thin films: A first-principles study. <i>Physical Review B</i> , 2014 , 89,	3.3	33
259	Influence of substrate type and quality on carrier mobility in graphene nanoribbons. <i>Journal of Applied Physics</i> , 2013 , 114, 053701	2.5	13
258	Electric-field-induced thermally assisted switching of monodomain magnetic bits. <i>Journal of Applied Physics</i> , 2013 , 113, 013912	2.5	24
257	Low-power non-volatile spintronic memory: STT-RAM and beyond. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 074003	3	308

256	High-quality Bi ₂ Te ₃ thin films grown on mica substrates for potential optoelectronic applications. <i>Applied Physics Letters</i> , 2013 , 103, 031605	3-4	44
255	Magnetically doped semiconducting topological insulators. <i>Journal of Applied Physics</i> , 2012 , 112, 063912	2.5	69
254	Reduction of switching current density in perpendicular magnetic tunnel junctions by tuning the anisotropy of the CoFeB free layer. <i>Journal of Applied Physics</i> , 2012 , 111, 07C907	2.5	26
253	Two dimensional crystal tunneling devices for THz operation. <i>Applied Physics Letters</i> , 2012 , 101, 263112	3-4	23
252	Nanoscale magnetic tunnel junction sensors with perpendicular anisotropy sensing layer. <i>Applied Physics Letters</i> , 2012 , 101, 062412	3-4	38
251	NONVOLATILE SPINTRONICS: PERSPECTIVES ON INSTANT-ON NONVOLATILE NANO-ELECTRONIC SYSTEMS. <i>Spin</i> , 2012 , 02, 1250009	1-3	24
250	Low writing energy and sub nanosecond spin torque transfer switching of in-plane magnetic tunnel junction for spin torque transfer random access memory. <i>Journal of Applied Physics</i> , 2011 , 109, 07C720	2-5	87
249	Switching current reduction using perpendicular anisotropy in CoFeB/MgO magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011 , 98, 112507	3-4	151
248	Effect of resistance-area product on spin-transfer switching in MgO-based magnetic tunnel junction memory cells. <i>Applied Physics Letters</i> , 2011 , 98, 072512	3-4	41
247	Epitaxial growth of high mobility Bi ₂ Se ₃ thin films on CdS. <i>Applied Physics Letters</i> , 2011 , 98, 242102	3-4	79
246	Deep subnanosecond spin torque switching in magnetic tunnel junctions with combined in-plane and perpendicular polarizers. <i>Applied Physics Letters</i> , 2011 , 98, 102509	3-4	76
245	Enhancement of microwave emission in magnetic tunnel junction oscillators through in-plane field orientation. <i>Applied Physics Letters</i> , 2011 , 99, 032503	3-4	37
244	Bias voltage dependence of magnetic tunnel junctions comprising amorphous ferromagnetic CoFeSiB layer with double barriers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 1847-1850	1-6	
243	Optical properties of Y ₂ O ₃ thin films doped with spatially controlled Er ³⁺ by atomic layer deposition. <i>Journal of Applied Physics</i> , 2007 , 101, 123116	2-5	21
242	Nanoscale modules with full spin-wave interconnectivity. <i>Journal of Experimental Nanoscience</i> , 2007 , 2, 73-86	1-9	2
241	Transport study of a single bismuth nanowire fabricated by the silver and silicon nanowire shadow masks. <i>Applied Physics Letters</i> , 2006 , 89, 141503	3-4	30
240	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. <i>Journal of Applied Physics</i> , 2006 , 99, 024504	2-5	12
239	Nanostructure and temperature-dependent photoluminescence of Er-doped Y ₂ O ₃ thin films for micro-optoelectronic integrated circuits. <i>Journal of Applied Physics</i> , 2006 , 100, 073512	2-5	23

238	Microstructural and optical properties of self-organized GaN quantum-dot assemblies. <i>Journal of Applied Physics</i> , 2005 , 97, 043527	2.5	7
237	Characterization of nanostructure in Si _{1-x} Ge _x epilayers using x-ray reflectivity and fluorescence techniques. <i>Journal of Applied Physics</i> , 2005 , 98, 074309	2.5	5
236	Tunable normal incidence Ge quantum dot midinfrared detectors. <i>Journal of Applied Physics</i> , 2004 , 96, 773-776	2.5	17
235	Interwell exciton dispersion engineering, coherent phonons generation and optical detection of exciton condensate. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 85-100	1.3	1
234	Quantum Computation by Electron Spin in SiGe Heterostructures 2004 , 465-476		1
233	Temperature effect on the formation of uniform self-assembled Ge dots. <i>Applied Physics Letters</i> , 2003 , 83, 2847-2849	3.4	38
232	Observation of magnetic-field-enhanced source current of accumulated p-channel metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2003 , 82, 3547-3549	3.4	2
231	Cross-plane thermal conductivity of self-assembled Ge quantum dot superlattices. <i>Physical Review B</i> , 2003 , 67,	3.3	40
230	Optical phonons in self-assembled Ge quantum dot superlattices: Strain relaxation effects. <i>Journal of Applied Physics</i> , 2002 , 92, 6804-6808	2.5	36
229	Measurements of anisotropic thermoelectric properties in superlattices. <i>Applied Physics Letters</i> , 2002 , 81, 3588-3590	3.4	118
228	Simultaneous measurements of Seebeck coefficient and thermal conductivity across superlattice. <i>Applied Physics Letters</i> , 2002 , 80, 1758-1760	3.4	93
227	Photoluminescence of InAs quantum dots coupled to a two-dimensional electron gas. <i>Journal of Electronic Materials</i> , 2001 , 30, 459-462	1.9	1
226	Infrared multispectral detection using Si/Si _x Ge _{1-x} quantum well infrared photodetectors. <i>Applied Physics Letters</i> , 2001 , 78, 495-497	3.4	19
225	Modification of the three-phonon Umklapp process in a quantum wire. <i>Applied Physics Letters</i> , 2001 , 79, 851-853	3.4	20
224	Towards Si _{1-x} Ge _x quantum-well resonant-state terahertz laser. <i>Applied Physics Letters</i> , 2001 , 79, 3909-3911	3.4	47
223	Response to Comment on Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices [Appl. Phys. Lett. 78, 1160 (2001)]. <i>Applied Physics Letters</i> , 2001 , 78, 1162-1163	3.4	4
222	Effective compliant substrate for low-dislocation relaxed SiGe growth. <i>Applied Physics Letters</i> , 2001 , 78, 1219-1221	3.4	30
221	Spin-wave utilization in a quantum computer. <i>Physical Review A</i> , 2001 , 64,	2.6	24

220	Compliant effect of low-temperature Si buffer for SiGe growth. <i>Applied Physics Letters</i> , 2001 , 78, 454-456.	4	38
219	High-quality strain-relaxed SiGe films grown with low temperature Si buffer. <i>Journal of Applied Physics</i> , 2001 , 89, 8279-8283	2.5	39
218	High-quality Ge films on Si substrates using Sb surfactant-mediated graded SiGe buffers. <i>Applied Physics Letters</i> , 2001 , 79, 3431-3433	3.4	37
217	Optical study of SiGe films grown with low temperature Si buffer. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 673, 1		
216	In-plane Thermal and Electronic Transport in Quantum Dot Superlattice. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 677, 491		
215	Study of phonons in self-organized multiple Ge quantum dots. <i>Journal of Electronic Materials</i> , 2000 , 29, 554-556	1.9	4
214	Investigation of flicker noise and deep-levels in GaN/AlGaIn transistors. <i>Journal of Electronic Materials</i> , 2000 , 29, 297-301	1.9	27
213	Low-dislocation relaxed SiGe grown on an effective compliant substrate. <i>Journal of Electronic Materials</i> , 2000 , 29, 950-955	1.9	9
212	Regimented placement of self-assembled Ge dots on selectively grown Si mesas. <i>Applied Physics Letters</i> , 2000 , 76, 3591-3593	3.4	85
211	High-quality strain-relaxed SiGe alloy grown on implanted silicon insulator substrate. <i>Applied Physics Letters</i> , 2000 , 76, 2680-2682	3.4	42
210	In-plane lattice thermal conductivity of a quantum-dot superlattice. <i>Journal of Applied Physics</i> , 2000 , 88, 696-699	2.5	86
209	Experimental proof-of-principle investigation of enhanced Z3DT in (001) oriented Si/Ge superlattices. <i>Applied Physics Letters</i> , 2000 , 77, 1490-1492	3.4	151
208	Thermoelectric figure of merit enhancement in a quantum dot superlattice. <i>Nanotechnology</i> , 2000 , 11, 327-331	3.4	47
207	Changes in luminescence emission induced by proton irradiation: InGaAs/GaAs quantum wells and quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 2074-2076	3.4	91
206	Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices. <i>Applied Physics Letters</i> , 2000 , 76, 586-588	3.4	50
205	Raman spectroscopy of electrochemically self-assembled CdS quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 137-139	3.4	120
204	Controlled arrangement of self-organized Ge islands on patterned Si (001) substrates. <i>Applied Physics Letters</i> , 1999 , 75, 2752-2754	3.4	132
203	Response to [Comment on Raman scattering from a self-organized Ge dot superlattice][Appl. Phys. Lett. 75, 3572 (1999)]. <i>Applied Physics Letters</i> , 1999 , 75, 3574-3575	3.4	13

202	Self-organized Ge quantum wires on Si(111) substrates. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 1406-1409	2.9	2
201	Effect of channel doping on the low-frequency noise in GaN/AlGaN heterostructure field-effect transistors. <i>Applied Physics Letters</i> , 1999 , 75, 2064-2066	3.4	31
200	Thermal relaxation processes probed by intersubband and inter-valence-band transitions in Si/Si _{1-x} Ge _x multiple quantum wells. <i>Applied Physics Letters</i> , 1999 , 75, 2232-2234	3.4	2
199	Raman scattering and infrared absorption in multiple boron-doped Ge dots. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 1420-1424	2.9	2
198	Observation of inter-sub-level transitions in modulation-doped Ge quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 1745-1747	3.4	28
197	Growth and study of self-organized Ge quantum wires on Si(111) substrates. <i>Applied Physics Letters</i> , 1999 , 74, 2471-2473	3.4	27
196	A surfactant-mediated relaxed Si _{0.5} Ge _{0.5} graded layer with a very low threading dislocation density and smooth surface. <i>Applied Physics Letters</i> , 1999 , 75, 1586-1588	3.4	62
195	Fabrication of nanometer size photoresist wire patterns with a silver nanocrystal shadowmask. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 1425-1427	2.9	11
194	Formation of nanometer-scale InAs islands on silicon. <i>Journal of Electronic Materials</i> , 1999 , 28, 432-436	1.9	14
193	Lateral Transport in Strained SiGe Quantum Wells Doped with Boron. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 211, 495-499	1.3	8
192	Intersubband absorption in boron-doped multiple Ge quantum dots. <i>Applied Physics Letters</i> , 1999 , 74, 185-187	3.4	87
191	Tunnel diodes fabricated from CdSe nanocrystal monolayers. <i>Applied Physics Letters</i> , 1999 , 74, 317-319	3.4	43
190	Raman scattering from a self-organized Ge dot superlattice. <i>Applied Physics Letters</i> , 1999 , 74, 1863-1865	3.4	43
189	Temperature-dependent morphology of three-dimensional InAs islands grown on silicon. <i>Applied Physics Letters</i> , 1999 , 75, 1273-1275	3.4	14
188	Inter-Sub-Level Spectroscopy of P-Type Modulation-Doped Ge Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 571, 15		
187	Mechanism of the Preferential Edge-Positioning of Self-Organized Ge Quantum Dots on Si Mesas. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 571, 31		1
186	Demonstration of Si homojunction far-infrared detectors. <i>Applied Physics Letters</i> , 1998 , 72, 2307-2309	3.4	24
185	Correlation between barrier height and band offsets in metal/Si _{1-x} Ge _x /Si heterostructures. <i>Applied Physics Letters</i> , 1998 , 73, 3920-3922	3.4	9

184	Persistent photoconductivity in Si delta-doped GaAs at low doping concentration. <i>Applied Physics Letters</i> , 1998 , 73, 3235-3237	3-4	6
183	Localized-state band induced by B Doping in Si/Si _{1-x} Gex/Si quantum wells. <i>Physical Review B</i> , 1998 , 57, 6579-6583	3-3	9
182	Experimental Study of Phonon-Folding in Si/Ge and Si/Sige Structures Designed for Thermoelectric Applications. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 545, 111		3
181	Thermal Conductivity and Phonon Engineering in Low-Dimensional Structures. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 545, 357		5
180	Experimental Study of the Effect of the Quantum Well Structures on the Thermoelectric Figure of Merit in Si/Si _{1-x} Gex System. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 545, 369		8
179	Far-infrared free-hole absorption in epitaxial silicon films for homojunction detectors. <i>Applied Physics Letters</i> , 1997 , 71, 515-517	3-4	13
178	SiGe quantum dots prepared on an ordered mesoporous silica coated Si substrate. <i>Applied Physics Letters</i> , 1997 , 71, 2448-2450	3-4	35
177	A Si bistable diode utilizing interband tunneling junctions. <i>Applied Physics Letters</i> , 1997 , 71, 2190-2192	3-4	7
176	Lattice modification and luminescence of dry-etched Si-Si _{1-x} Gex quantum dots 1997 , 3007, 170		5
175	Observation of new type resonances in triple barrier resonant tunneling diodes. <i>Journal of Applied Physics</i> , 1997 , 82, 2980-2983	2-5	1
174	Strain-conserving doping of a pseudomorphic metastable Ge _{0.06} Si _{0.94} layer on Si(100) by low-dose BF ₂ ⁺ implantation. <i>Journal of Applied Physics</i> , 1997 , 81, 1695-1699	2-5	7
173	Quantum Confinement Effects on the Thermoelectric Figure of Merit in Si/Si _{1-x} Gex System. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 478, 169		1
172	Prospects for High Thermoelectric Figures of Merit in 2D Systems. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 478, 55		9
171	Free Carrier Absorption in P-Type Epitaxial Si and GaAs Films for far-Infrared Detection. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 484, 199		
170	Control of Sizes and Optical Emission of Sige Quantum Dots Prepared on Ordered Mesoporous Silica Coated Si Wafer. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 486, 255		2
169	Effect of doping density on capacitance of resonant tunneling diodes. <i>Journal of Applied Physics</i> , 1997 , 82, 5206-5209	2-5	1
168	Pressure and strain sensors based on intervalley electron transfer in AlGaAs. <i>Applied Physics Letters</i> , 1997 , 70, 3437-3439	3-4	2
167	Facet Formation in Submicron Selective Growth of Si/SiGe. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 448, 241		0

166	Effect of Quantum-Well Structures on the Thermoelectric Figure of Merit in the Si/Si _{1-x} Ge _x System. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 452, 261		6
165	SiGe band engineering for MOS, CMOS and quantum effect devices. <i>Journal of Materials Science: Materials in Electronics</i> , 1995 , 6, 311-324	2.1	35
164	Reduction of the dislocation density for GaAs thin films on Si substrates grown by molecular beam epitaxy using the two-step growth method. <i>Journal of Materials Science Letters</i> , 1995 , 14, 1340-1343		
163	Chemical Etching of Si _{1-x} Ge _x in HF : H ₂ O ₂ : CH ₃ COOH. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 1260-1266	3.9	67
162	Interfacial roughness scaling and strain in lattice mismatched Si _{0.4} Ge _{0.6} thin films on Si. <i>Applied Physics Letters</i> , 1995 , 67, 629-631	3.4	14
161	Vertical transport in GaAs/Al _x Ga _{1-x} As superlattices by a microwave time-of-flight technique. <i>Physical Review B</i> , 1995 , 51, 17614-17617	3.3	3
160	Strain transfer between thin films on buried oxide and its application in heteroepitaxial crystal growth. <i>Philosophical Magazine Letters</i> , 1995 , 72, 231-237	1	9
159	GeSi/Si bistable diode exhibiting a large on/off conductance ratio. <i>Applied Physics Letters</i> , 1995 , 66, 2403-2405	3.4	3
158	Normal-incidence strained-layer superlattice Ge _{0.5} Si _{0.5} /Si photodiodes near 1.3 μ m. <i>Applied Physics Letters</i> , 1995 , 67, 566-568	3.4	53
157	Dependence of damage and strain on the temperature of Si irradiation in epitaxial Ge _{0.10} Si _{0.90} films on Si(100). <i>Journal of Applied Physics</i> , 1995 , 77, 2329-2338	2.5	11
156	Microstructure of Oxidized Ge _{0.78} Si _{0.12} annealed in a Reducing Ambient. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 379, 127		
155	Solid-Phase Epitaxial Regrowth and Dopant Activation of Arsenic. Implanted Metastable Pseudomorphic Ge _{0.08} Si _{0.92} AND Ge _{0.16} Si _{0.84} ON Si(100). <i>Materials Research Society Symposia Proceedings</i> , 1995 , 379, 467		
154	Nanometer-structure writing on Si(100) surfaces using a non-contact-mode atomic force microscope. <i>Applied Physics Letters</i> , 1994 , 65, 1415-1417	3.4	31
153	Transfer-matrix analysis of waveguide phase modulator using the linear electro-optic effect of asymmetric quantum wells. <i>Journal of Applied Physics</i> , 1994 , 76, 4903-4905	2.5	1
152	Boron delta doping in Si and SiGe and its application toward field-effect transistor devices. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994 , 12, 1203		10
151	Nanometer scale patterning of silicon (100) surfaces by an atomic force microscope operating in air. <i>Applied Physics Letters</i> , 1994 , 64, 2133-2135	3.4	66
150	Observation of a large capacitive current in a double barrier resonant tunneling diode at resonance. <i>Applied Physics Letters</i> , 1994 , 64, 2276-2278	3.4	11
149	Interface properties of thin oxides grown on strained Ge _x Si _{1-x} layer. <i>Journal of Applied Physics</i> , 1994 , 76, 982-986	2.5	21

148	Strain relief of metastable GeSi layers on Si(100). <i>Journal of Applied Physics</i> , 1994 , 75, 4475-4481	2.5	24
147	Intermixing problems of symmetrical strained Si/Ge monolayer superlattices grown by molecular beam epitaxy. <i>Physica Status Solidi A</i> , 1994 , 144, K31-K35		
146	Damage and strain in pseudomorphic vs relaxed $GexSi_{1-x}$ layers on Si(100) generated by Si ion irradiation. <i>Journal of Electronic Materials</i> , 1994 , 23, 369-373	1.9	9
145	Epitaxial Ge layers on Si via $GexSi_{1-x}O_2$ reduction: The roles of the hydrogen partial pressure and the Ge content. <i>Journal of Electronic Materials</i> , 1994 , 23, 437-440	1.9	4
144	Electron intersubband absorption in Ge/Si $_{1-x}$ Gex quantum-well structures grown on Si (001) substrate. <i>Applied Physics Letters</i> , 1994 , 64, 1256-1258	3.4	12
143	Dominant photogenerated valley current in a double-barrier resonant-tunneling diode. <i>Applied Physics Letters</i> , 1994 , 65, 2999-3001	3.4	4
142	Steady-State Versus Rapid Thermal Annealing of Phosphorusimplanted Pseudomorphic Si(100)/Ge $_{0.12}$ Si $_{0.88}$. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 342, 51		2
141	Variations of Interfacial Roughness with Epilayer Thickness and Scaling Behavior in Si $_{1-x}$ Gex, Grown on Si(100) Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 367, 311		
140	Carrier transport in GaAs/AlGaAs heterostructures by microwave time-of-flight technique. <i>Applied Physics Letters</i> , 1993 , 63, 3491-3493	3.4	2
139	Intersubband transitions in a p-type delta -doped SiGe/Si quantum well. <i>Physical Review B</i> , 1993 , 47, 15638-15643	3.4	4
138	Effect of hydrogenation on the luminescence of strained Si $_{1-x}$ Gex alloy layers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1993 , 74, 1279-1282	2.5	6
137	Electron mobility enhancement from coupled wells in delta-doped GaAs. <i>Applied Physics Letters</i> , 1993 , 62, 504-506	3.4	57
136	Bound-to-bound intersubband transitions in a δ -doped p-type Si/SixGe $_{1-x}$ /Si quantum well. <i>Applied Physics Letters</i> , 1993 , 62, 1119-1121	3.4	6
135	Boron delta-doped Si metal semiconductor field-effect transistor grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 1363-1365	3.4	13
134	Ballistic-electron-emission microscopy of (100)CoGa/n-type GaAs interfaces grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 1062-1064	3.4	3
133	Damage and strain in epitaxial $GexSi_{1-x}$ films irradiated with Si. <i>Journal of Applied Physics</i> , 1993 , 74, 6039-6045	2.5	49
132	Nanocrystalline Ge in SiO $_2$ by annealing of $GexSi_{1-x}O_2$ in hydrogen. <i>Applied Physics Letters</i> , 1993 , 62, 3321-3323	3.4	31
131	Observation of magnetic-field-induced delocalization: Transition from Anderson insulator to quantum Hall conductor. <i>Physical Review Letters</i> , 1993 , 71, 1439-1442	7.4	152

130	Enhancement of Si hole mobility in coupled delta-doped wells. <i>Applied Physics Letters</i> , 1993 , 62, 3455-3457		18
129	Microscopic structure of interfaces in Si _{1-x} Ge _x /Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield. <i>Physical Review B</i> , 1993 , 47, 16373-16381	3.3	82
128	Band structure and symmetry analysis of coherently grown Si _{1-x} Ge _x alloys on oriented substrates. <i>Physical Review B</i> , 1993 , 47, 1936-1953	3.3	49
127	Characterization of Si _{1-x} Ge _x /Si heterostructures for device applications using spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1993 , 74, 586-595	2.5	9
126	Photoluminescence and optically detected magnetic resonance of Si/Si _{1-x} Ge _x strained-layer superlattices grown by molecular-beam epitaxy. <i>Physical Review B</i> , 1993 , 47, 1305-1315	3.3	24
125	Dopant Activation and Epitaxial Regrowth in P-Implanted Pseudomorphic Ge _{0.12} Si _{0.88} Layers On Si(100). <i>Materials Research Society Symposia Proceedings</i> , 1993 , 321, 485		6
124	Photoluminescence studies on GaAs/Ge/Si and GaAs/SiGe/Ge/Si heterostructures after annealing and hydrogenation. <i>Physica Status Solidi A</i> , 1993 , 139, 443-449		1
123	High-mobility p-channel metal-oxide-semiconductor field-effect transistor on strained Si. <i>Applied Physics Letters</i> , 1993 , 62, 2853-2855	3.4	123
122	Interband resonant tunneling in InAs/AlSb/GaSb symmetric polytype structures. <i>Physical Review B</i> , 1992 , 46, 16012-16017	3.3	37
121	Oscillator strength for intersubband transitions in strained n-type Si _{1-x} Ge _x quantum wells. <i>Physical Review B</i> , 1992 , 46, 7682-7690	3.3	14
120	Intervalence-subband transition in SiGe/Si multiple quantum wells—normal incident detection. <i>Applied Physics Letters</i> , 1992 , 61, 681-683	3.4	62
119	Luminescence of strained Si _{1-x} Ge _x alloy layers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992 , 61, 2586-2588	3.4	12
118	Intersubband absorption in Sb doped molecular beam epitaxy Si quantum well structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 992		7
117	Structural characterization of Si _m Ge _n strained layer superlattices. <i>Journal of Applied Physics</i> , 1992 , 71, 4305-4313	2.5	7
116	Growth of SiC film on Si substrate by surface reaction using hydrocarbon gas and Si molecular beams in ultrahigh vacuum. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 930		17
115	Importance of sample preheating in oxidation of Ge _x Si _{1-x} . <i>Journal of Applied Physics</i> , 1992 , 71, 3626-3627	2.5	4
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